

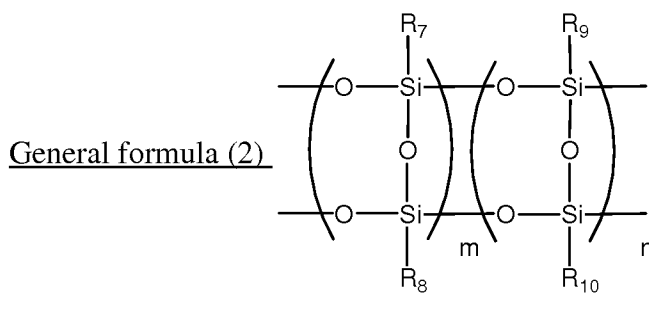
IN THE CLAIMS:

Please cancel Claims 2, 3, and 11 to 37 without prejudice to or disclaimer of the subject matter presented therein. Please amend Claims 1 and 4 to 10 as shown below.

1. (Currently Amended) A field effect transistor having an organic semiconductor layer, comprising:

an organic semiconductor layer containing at least porphyrin; and

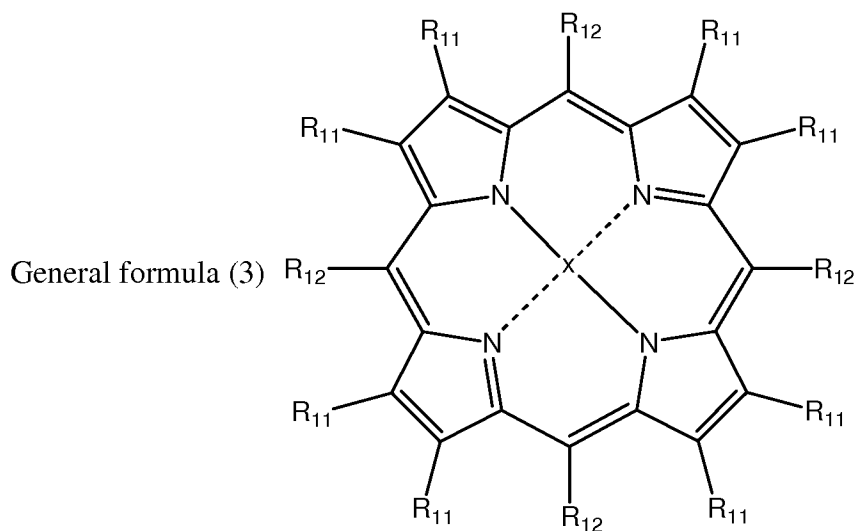
a layer ~~composed of at least a polysiloxane compound, the layer being laminated on the organic semiconductor layer so as to be in intimate contact with the organic semiconductor layer~~ consisting essentially of a silsesquioxane compound represented by the following general formula (2):



where R_7 to R_{10} each represents a substituted or unsubstituted alkyl or alkenyl group having 1 to 5 carbon atoms, or a substituted or unsubstituted phenyl group; R_7 to R_{10} may be identical to or different from one another; m and n each represents an integer of 0 or more; and a sum of m and n is an integer of 1 or more.

2 to 3. (Cancelled)

4. (Currently Amended) The field effect transistor according to ~~any one of claims 1 to 3~~ claim 3, wherein the porphyrin is represented by the following general formula (3):



~~(In the formula, where~~ R₁₁'s represent at least one kind selected from the group consisting of a hydrogen atom, a halogen atom, a hydroxyl group, or an alkyl, oxyalkyl, thioalkyl, or alkylester group having 1 to 12 carbon ~~atoms; atoms, and~~ R₁₁'s may be identical to or different from one ~~another. In addition, another;~~ adjacent R₁₁'s may form an aromatic ring which may have a ~~substituent. In addition, substituent;~~ the adjacent R₁₁'s may be connected to another porphyrin ring which may have a substituent through the formed aromatic ~~ring. ring;~~ R₁₂'s represent at least one kind selected from the group consisting of a hydrogen atom and an aryl group which may have a ~~substituent. substituent;~~ R₁₂'s may be

identical to or different from one ~~another~~; another; and X represents a hydrogen atom or a metal ~~atom~~. atom.

5. (Currently Amended) The field effect transistor according to ~~any one of claims 1 to 4~~ claim 4, wherein at least one pair of the adjacent R₁₁'s in the general formula (3) forms an aromatic ring.

6. (Currently Amended) The field effect transistor according to ~~any one of claims 1 to 5~~ claim 5, wherein the aromatic ring formed by the at least one pair of the adjacent R₁₁'s in the general formula (3) is obtained by heating a precursor having a bicyclo [2.2.2] octadiene skeleton structure which may have a substituent.

7. (Currently Amended) ~~The~~ A field effect transistor ~~according to any one of claims 1 to 6~~; having an organic semiconductor layer, comprising:

an organic semiconductor layer containing at least porphyrin; and

a layer composed of at least a polysiloxane compound, the layer being laminated on the organic semiconductor layer so as to be in intimate contact with the organic semiconductor layer.

wherein Bragg angles (2θ) of CuKα X-ray diffraction in the organic semiconductor layer have peaks at 8.3° ± 0.2°, 10.1° ± 0.2°, 11.8° ± 0.2°, and 14.4° ± 0.2°.

8. (Currently Amended) ~~The~~ A field effect transistor ~~according to any one~~

of claims 1 to 6; having an organic semiconductor layer, comprising:

an organic semiconductor layer containing at least porphyrin; and

a layer composed of at least a polysiloxane compound, the layer being laminated on the organic semiconductor layer so as to be in intimate contact with the organic semiconductor layer,

wherein Bragg angles (2θ) of CuK α X-ray diffraction in the organic semiconductor layer have peaks at $8.4^\circ \pm 0.2^\circ$, $11.9^\circ \pm 0.2^\circ$, and $16.9^\circ \pm 0.2^\circ$.

9. (Currently Amended) ~~The A~~ field effect transistor ~~according to any one of claims 1 to 6;~~ having an organic semiconductor layer, comprising:

an organic semiconductor layer containing at least porphyrin; and

a layer composed of at least a polysiloxane compound, the layer being laminated on the organic semiconductor layer so as to be in intimate contact with the organic semiconductor layer,

wherein Bragg angles (2θ) of CuK α X-ray diffraction in the organic semiconductor layer have peaks at $7.2^\circ \pm 0.2^\circ$, $7.8^\circ \pm 0.2^\circ$, $11.7^\circ \pm 0.2^\circ$, and $23.5^\circ \pm 0.2^\circ$.

10. (Currently Amended) ~~The A~~ field effect transistor ~~according to any one of claims 1 to 6;~~ having an organic semiconductor layer, comprising:

an organic semiconductor layer containing at least porphyrin; and

a layer composed of at least a polysiloxane compound, the layer being laminated on the organic semiconductor layer so as to be in intimate contact with the

organic semiconductor layer.

wherein Bragg angles (2θ) of CuK α X-ray diffraction in the organic semiconductor layer have peaks at $7.3^\circ \pm 0.2^\circ$, $7.8^\circ \pm 0.2^\circ$, $11.7^\circ \pm 0.2^\circ$, and $19.6^\circ \pm 0.2^\circ$.

11 to 37. (Cancelled)